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Altri autori (Persone)	BrillsonL. J
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Sommario/riassunto	The authors present the state of the art in growing, processing, and characterizing electronic junctions. Overall, they have assembled a broad array of the latest semiconductor interface science and technology, ranging from advanced ohmic, Schottky, and heterojunction contacts to the refined perspectives of microscopic junctions gleaned from ultrahigh vacuum surface science techniques. Considerable progress has been made in these areas over the last few years. This book is intended for technologists and solid state researchers alike.

